

Debin Hou

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	A Variable Gain Power Amplifier Based on Switched-Capacitor Array With Stable Linearity. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 289-293.	2.2	2
2	An E-Band SiGe High Efficiency, High Harmonic Suppression Amplifier Multiplier Chain With Wide Temperature Operating Range. IEEE Transactions on Circuits and Systems I: Regular Papers, 2022, 69, 1041-1050.	3.5	6
3	A Wide Tuning Range Low-Phase-Noise Ku/Ka Dual Bands SiGe VCO Based on Transformer-Coupled Tank. IEEE Microwave and Wireless Components Letters, 2022, 32, 437-440.	2.0	4
4	A 37-GHz Asymmetric Doherty Power Amplifier With 28-dBm P_{sat} and 32% Back-Off PAE in 0.1- μm GaAs Process. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 1391-1400.	2.9	6
5	A Linearity-Enhanced 18.7-36.5-GHz LNA With 1.5-2.1-dB NF for Radar Applications. IEEE Microwave and Wireless Components Letters, 2022, 32, 972-975.	2.0	11
6	Research on Silicon-Based Terahertz Communication Integrated Circuits. Chinese Journal of Electronics, 2022, 31, 516-533.	0.7	1
7	W-band Scalable 2-Phased-Array Transmitter and Receiver Chipsets in SiGe BiCMOS for High Data-Rate Communication. IEEE Journal of Solid-State Circuits, 2022, 57, 2685-2701.	3.5	5
8	Towards 6G wireless communication networks: vision, enabling technologies, and new paradigm shifts. Science China Information Sciences, 2021, 64, 1.	2.7	858
9	A Broadband Power Amplifier in 130-nm SiGe BiCMOS Technology. IEEE Solid-State Circuits Letters, 2021, 4, 44-47.	1.3	11
10	A 300-GHz Transmitter Front End With 4.1-dBm Peak Output Power for Sub-THz Communication Using 130-nm SiGe BiCMOS Technology. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 4925-4936.	2.9	14
11	A 220-GHz Power Amplifier With 22.5-dB Gain and 9-dBm P_{sat} in 130-nm SiGe. IEEE Microwave and Wireless Components Letters, 2021, 31, 1166-1169.	2.0	9
12	The Role of Millimeter-Wave Technologies in 5G/6G Wireless Communications. IEEE Journal of Microwaves, 2021, 1, 101-122.	4.9	312
13	A High Linearity W-Band LNA With 21-dB Gain and 5.5-dB NF in 0.13 μm SiGe BiCMOS. , 2021, , .		4
14	Millimeter-wave wireless communications for home network in fiber-to-the-room scenario. Frontiers of Information Technology and Electronic Engineering, 2021, 22, 441-456.	1.5	3
15	A Ka-Band Switchable LNA With 2.4-dB NF Employing a Varactor-Based Tunable Network. IEEE Microwave and Wireless Components Letters, 2021, 31, 385-388.	2.0	22
16	A W-band preamplified MMIC power detector for passive imaging applications. Microwave and Optical Technology Letters, 2021, 63, 1875-1880.	0.9	0
17	A Wide Tuning Range low Kvco Ka-Band BiCMOS LC-VCO Using Varactor Bank. , 2021, , .		3
18	A Two-Chip Cascaded FMCW Radar For 2D Angle Estimation. , 2021, , .		5

#	ARTICLE	IF	CITATIONS
19	Analysis and Design of D-band High Output Power Signal Sources in 130-nm SiGe BiCMOS Process. , 2021, , .		1
20	A 230-GHz SiGe Amplifier With 21.8-dB Gain and 3-dBm Output Power for Sub-THz Receivers. IEEE Microwave and Wireless Components Letters, 2021, 31, 1004-1007.	2.0	7
21	A High-Linearity Adaptive-Bias SiGe Power Amplifier for 5G Communication. IEEE Transactions on Circuits and Systems II: Express Briefs, 2021, 68, 2770-2774.	2.2	7
22	A \sim 28.5-dB EVM 64-QAM 45-GHz Transceiver for IEEE 802.11aj. IEEE Journal of Solid-State Circuits, 2021, 56, 3077-3093.	3.5	9
23	A 24 \times 30-GHz TRX Front-End With High Linearity and Load-Variation Insensitivity for mm-Wave 5G in 0.13- μ m SiGe BiCMOS. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 4561-4575.	2.9	22
24	A K-Band FMCW Frequency Synthesizer Using Q-Boosted Switched Inductor VCO in SiGe BiCMOS for 77 GHz Radar Applications. Electronics (Switzerland), 2020, 9, 1933.	1.8	3
25	A Low-Loss Fan-Out Wafer-Level Package With a Novel Redistribution Layer Pattern and Its Measurement Methodology for Millimeter-Wave Application. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2020, 10, 1073-1078.	1.4	7
26	A 64-QAM 45-GHz SiGe Transceiver for IEEE 802.11aj. , 2020, , .		5
27	A 143.2 \times 168.8-GHz signal source with 5.6 dBm peak output power in a 130-nm SiGe BiCMOS process. Science China Information Sciences, 2020, 63, 1.	2.7	2
28	A 250-GHz Differential SiGe Amplifier With 21.5-dB Gain for Sub-THz Transmitters. IEEE Transactions on Terahertz Science and Technology, 2020, 10, 624-633.	2.0	25
29	Design and Implementation of a Full-Digital Beamforming Array With Nonreciprocal Tx/Rx Beam Patterns. IEEE Antennas and Wireless Propagation Letters, 2020, 19, 1978-1982.	2.4	19
30	A W-Band 6-Bit Phase Shifter With 7 dB Gain and 1.35 $^\circ$ RMS Phase Error in 130 nm SiGe BiCMOS. IEEE Transactions on Circuits and Systems II: Express Briefs, 2020, 67, 1839-1843.	2.2	19
31	A 273.5 \times 312-GHz Signal Source With 2.3 dBm Peak Output Power in a 130-nm SiGe BiCMOS Process. IEEE Transactions on Terahertz Science and Technology, 2020, 10, 260-270.	2.0	8
32	Transformer matched gilbert mixer with active balun for D band transmitter. Microwave and Optical Technology Letters, 2020, 62, 2696-2702.	0.9	2
33	A 150-GHz Transmitter With 12-dBm Peak Output Power Using 130-nm SiGe:C BiCMOS Process. IEEE Transactions on Microwave Theory and Techniques, 2020, 68, 3056-3067.	2.9	20
34	W \times band out \times of \times phase active power divider with continuously tunable power division ratio and invariant phase difference. Electronics Letters, 2020, 56, 178-180.	0.5	1
35	A Wide-Bandwidth W-Band LNA in GaAs 0.1 μ m pHEMT Technology. , 2020, , .		4
36	E \times band power detector with robust temperature performance in 130 \AA m SiGe BiCMOS. Electronics Letters, 2019, 55, 733-735.	0.5	0

#	ARTICLE	IF	CITATIONS
37	A 280-325 GHz Frequency Multiplier Chain With 2.5 dBm Peak Output Power. , 2019, , .		22
38	A Dual-Band Switchable MMIC Star Mixer. IEEE Microwave and Wireless Components Letters, 2019, 29, 737-740.	2.0	9
39	A high-efficiency, high harmonic rejection E-band SiGe HBT frequency tripler for high-resolution radar application. Science China Information Sciences, 2019, 62, 1.	2.7	2
40	K-Band Low Phase Noise VCO Based on Q-Boosted Switched Inductor. Electronics (Switzerland), 2019, 8, 1132.	1.8	4
41	A Q-Band Self-Biased LNA in 0.1- μm GaAs pHEMT Technology. , 2019, , .		6
42	A Wideband W-Band Driver Amplifier in 0.1 μm GaAs Process. , 2019, , .		5
43	A 270 GHz $\times 9$ Multiplier Chain MMIC With On-Chip Dielectric-Resonator Antenna. IEEE Transactions on Terahertz Science and Technology, 2018, 8, 224-230.	2.0	37
44	Research Progress of the Circuits for the THz Systems. , 2018, , .		1
45	A 28 GHz Low Phase-Noise Colpitts VCO with Wide Tuning-Range in SiGe Technology. , 2018, , .		9
46	A 300 GHz 4th-Harmonic Mixer in $0.13 \mu\text{m}$ SiGe BiCMOS Technology. , 2018, , .		1
47	A W-band wideband power amplifier using out-of-phase divider in 0.13- μm SiGe BiCMOS. Science China Information Sciences, 2018, 61, 1.	2.7	0
48	A High-Efficiency E-band SiGe HBT Frequency Tripler with Broadband Performance. , 2018, , .		20
49	A compact D-band I/Q mixer with improved transformer balun. Microwave and Optical Technology Letters, 2017, 59, 2840-2844.	0.9	6
50	Design and implementation of A Ka-Band MMIC driver amplifier and module. , 2017, , .		1
51	Design of silicon based millimeter wave oscillators. , 2016, , .		1
52	D-band on-chip higher-order-mode dielectric-resonator antennas fed by half-mode cavity in CMOS technology. IEEE Antennas and Propagation Magazine, 2014, 56, 80-89.	1.2	55
53	CMOS hybrid couplers with improved phase inverter structure for D-band applications. IET Microwaves, Antennas and Propagation, 2013, 7, 569-574.	0.7	6
54	130-GHz On-Chip Meander Slot Antennas With Stacked Dielectric Resonators in Standard CMOS Technology. IEEE Transactions on Antennas and Propagation, 2012, 60, 4102-4109.	3.1	83

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55	Distributed Modeling of Six-Port Transformer for Millimeter-Wave SiGe BiCMOS Circuits Design. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 3728-3738.	2.9	31
56	A D-Band Cascode Amplifier With 24.3 dB Gain and 7.7 dBm Output Power in 0.13 μm SiGe BiCMOS Technology. IEEE Microwave and Wireless Components Letters, 2012, 22, 191-193.	2.0	41
57	Silicon Based Millimeter Wave and THz ICs. IEICE Transactions on Electronics, 2012, E95.C, 1134-1140.	0.3	4